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## An Absorber-coupled TES Bolometer for Measuring CMB Polarization

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### Abstract

We report an absorber-coupled superconducting Transition Edge Sensor (TES) bolometric polarimeter for measuring Cosmic Microwave Background (CMB) B-mode polarization. The polarimeter consists of a dipole-like PdAu absorber and a Mo/Au bi-layer TES on a suspended silicon nitride rectangle. Its design, fabrication, thermal properties, and optical performance are presented.

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### 1. Introduction

Superconducting TES bolometers can be used to measure thermal fluctuations on the sky through a variety of radiation coupling mechanisms [1]. A TES operated with negative electro-thermal feedback

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under a voltage bias can be tuned to have a fast response time and a noise level below the photon shot noise [1-3]. Therefore a TES bolometer, with appropriate optical coupling, has the performance required to conduct sensitive observation of the cosmic microwave background radiation.

We have developed an absorber-coupled TES bolometric polarimeter with a 30% optical bandwidth at 90 GHz. An array of 180 of these polarimeters will be deployed on the South Pole Telescope (SPT) as part of a new polarization camera for the SPTpol experiment. The two key scientific goals of SPTpol are to detect the CMB B-mode polarization induced by inflationary gravitational waves, which would provide a direct measurement of the energy scale of inflation [4-5], and to measure the sum of neutrino masses through gravitational lensing of the CMB by large-scale structures in the universe [6].

## 2. Detector Design and Fabrication

The absorber-coupled polarimeter is designed for 90 GHz and consists of a dipole-like photon absorber for optical coupling and a Mo/Au bi-layer superconducting TES for thermal energy readout on a 1  $\mu\text{m}$  thick  $\text{Si}_3\text{N}_4$  rectangle. Four 10  $\mu\text{m}$  wide and 640  $\mu\text{m}$  long  $\text{Si}_3\text{N}_4$  legs at the TES sensor side and two 10  $\mu\text{m}$  wide and 640  $\mu\text{m}$  long  $\text{Si}_3\text{N}_4$  legs at the opposite side support the rectangle and serve as the weak thermal link to the cryogenic heat bath. The thermal conductance is  $G=170$  pW/K at 530 mK, which has a phonon noise comparable to the photon noise for ground-based observations. Fig. 1 (a) is a single-polarization detector. The dual-polarization pixel is a face-to-face setup of two single-polarization detectors perpendicular to each other and with a separation of 40  $\mu\text{m}$ .

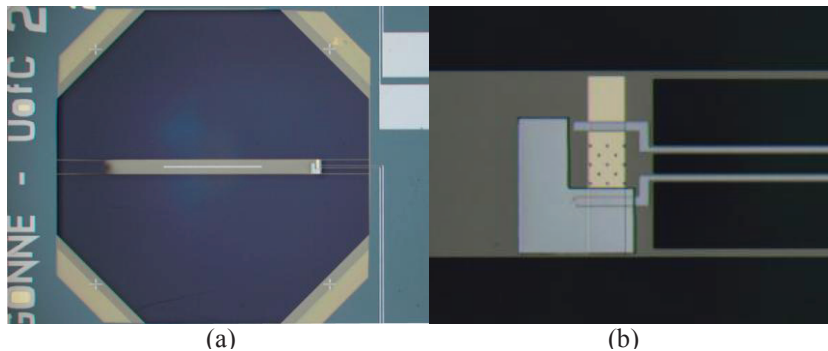


Fig. 1. (a) A 90 GHz absorber-coupled TES polarimeter. A 1320  $\mu\text{m}$  by 18  $\mu\text{m}$  dipole-like PdAu absorber is in the middle of the 2940  $\mu\text{m}$  by 200  $\mu\text{m}$   $\text{Si}_3\text{N}_4$  rectangle with six support legs. A TES is at the right end of the rectangle; (b) A magnified picture of the TES, which is 70  $\mu\text{m}$  by 40  $\mu\text{m}$  between the leads. The Nb dots on the top are for modifying TES superconducting transition width. For stable operation an additional thermal mass of 400 nm thick PdAu bling is connected to the TES at the lower side.

For the polarimeter, the beam is defined by a feed horn and telescope optics, which couples radiation from the sky into a circular waveguide. The band-pass is defined at the low end by the waveguide cut-off and at the high end by a free space metal mesh filter placed in front of the horn. The radiation in the waveguide is coupled to the TES through the absorber located on a  $\text{Si}_3\text{N}_4$  membrane which spans the guide  $\lambda/4$  from a backshort. A waveguide choke prevents the fields from leaking out of the guide where the membrane penetrates. This design was optimized using High Frequency Structure Simulator (HFSS) to have a larger than 95% co-polar coupling and a less than 1% cross-polar coupling across the entire band. The present design uses a 78 GHz waveguide cut-off and a 110 GHz metal mesh low pass filter.

The detector fabrication is performed at the Materials Science Division and at the Center for Nanoscale Materials, Argonne National Laboratory. We purchase commercial 250  $\mu\text{m}$  thick silicon wafers with 1

$\mu\text{m}$  thick low stress silicon nitride on both sides from Rogue Valley Microelectronics. First we fabricate the Mo/Au bi-layer superconducting TES sensor with DC magnetron sputtering and standard photolithography techniques. The Mo is 22 nm thick, and Au 30 nm thick. The Nb dots on top of the TES and the 5  $\mu\text{m}$  wide and 120 nm thick Nb leads are patterned with lift-off. Next the PdAu absorber is fabricated with DC magnetron sputtering and lift-off. The thickness of PdAu is chosen to give a sheet impedance of  $5.3 \Omega/\square$  at operational cryogenic temperature. HFSS simulation shows that this impedance optimizes optical absorption of the polarimeter. The silicon behind the rectangle and the support legs is removed by KOH etching. The  $\text{Si}_3\text{N}_4$  legs are patterned with Reactive Ion Etch (RIE).

## 2. Detector Thermal Properties

The bolometric detector thermal conductance is defined by  $\text{Si}_3\text{N}_4$  support beams dimension and thermal conductivity. For a given  $\text{Si}_3\text{N}_4$  beam, its thermal conductance is

$$G = \kappa A/L, \quad (1)$$

where  $L$  is the beam length,  $A$  is cross section,  $\kappa$  is thermal conductivity. In the phonon gas kinetic theory,

$$\kappa = ClS/3, \quad (2)$$

where  $C$  is  $\text{Si}_3\text{N}_4$  volume heat capacity,  $l$  is phonon mean free path, and  $S=6986 \text{ m/s}$  is the average  $\text{Si}_3\text{N}_4$  sound speed calculated with its longitudinal and transverse sound speeds [7].

$\text{Si}_3\text{N}_4$  thermal conductivity is investigated using tailored thermal structures with TES on an island [8]. Empirically, the heat power flow along the beam as a function of bath temperature for a defined thermal structure is fitted as a power law [9-12] of

$$P = K(T^n - T_b^n), \quad (3)$$

where coefficient  $K$  and temperature power index  $n$  characterize thermal conductance,  $T$  is the temperature at the sensor,  $T_b$  is the bath temperature. In our investigation temperature range, we assume a power law dependence of thermal conductivity on temperature. The thermal conductance is the first derivative of the power over temperature,

$$G = nKT^{n-1}. \quad (4)$$

Therefore, thermal conductivity is connected with experimental data using equations (1) and (4) as

$$\kappa = (L/A)nKT^{n-1}. \quad (5)$$

For the polarimeter in Fig.1 (a), assuming that heat conduction obeys equation (3) for a single support beam and the PdAu absorber is isothermal, TES Joule heating power as a function of bath temperature is

$$P = 4K(T^n - T_b^n) + G_1 \frac{G_2 2K(T^n - T_b^n) - P_0(G_2 + 2nKT^{n-1})}{(G_1 + G_2)(G_2 + 2nKT^{n-1}) - G_2^2}, \quad (6)$$

where  $T$  is TES temperature,  $P_0=0$  is optical power in dark test,  $G_1$  is the thermal conductance from the TES to the absorber,  $G_2$  is the thermal conductance from the absorber to the end of the rectangle on the left. The values of  $G_1$  and  $G_2$  are estimated using TES temperature, the polarimeter dimensions and model data from reference [8] to the first order.

We have made and tested tailored thermal structures with 10  $\mu\text{m}$  to 30  $\mu\text{m}$  beam width, and five types of polarimeters. Four of the polarimeters have  $\text{Si}_3\text{N}_4$  beams widths of 10  $\mu\text{m}$ , 12  $\mu\text{m}$ , 15  $\mu\text{m}$  and 20  $\mu\text{m}$ . The fifth polarimeter has two different beam width: two 30  $\mu\text{m}$  beams and two 15  $\mu\text{m}$  beams at the TES

side, and two 30  $\mu\text{m}$  beams at the far side [13]. TES transition temperature varies from 460 mK to 550 mK, and we vary the cryogenic bath temperature from 300 mK to close to TES transition temperature. The thermal conductivities for a variety of beams at 450 mK are shown in Fig. 2 (a). There are three classes of data. The crosses are the thermal tested structures [8] and the circles are the polarimeters [13] with  $\text{Si}_3\text{N}_4$  grown on B1562, a common commercial 250  $\mu\text{m}$  Si wafer. Finally the squares are the polarimeters with  $\text{Si}_3\text{N}_4$  grown on B3663 which is high quality  $250\pm 5$   $\mu\text{m}$  Si wafer.

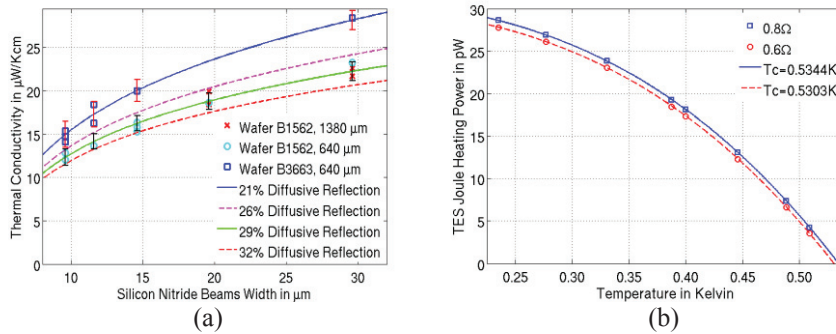


Fig. 2. Beam width dependence of thermal conductivity of 1  $\mu\text{m}$   $\text{Si}_3\text{N}_4$  at 0.450 K. The beam width is shifted down 0.4  $\mu\text{m}$  from nominal values because of side etching effects; (b) TES Joule heating power as a function of bath temperature using equation (6) at TES resistance of 0.8  $\Omega$  ( $K=34.15$  pW/ $K^n$ ,  $n=2.98$ ) and 0.6  $\Omega$  ( $K=34.05$  pW/ $K^n$ ,  $n=2.98$ ) respectively for a polarimeter in Fig. 1.

The boundary limited phonon transport model [14] is used to interpret the data. The green central line for the data of wafer B1562 is the model at 29% surface diffusive reflection of phonons. The two dashed lines show that the thermal conductivity is in  $\pm 3\%$  surface diffusive reflection range. The phonon mean free path is estimated to be 6.58  $\mu\text{m}$ , 9.80  $\mu\text{m}$  and 11.55  $\mu\text{m}$  for beams with width of 10  $\mu\text{m}$ , 20  $\mu\text{m}$  and 30  $\mu\text{m}$  respectively for wafer B1562. In the theory of boundary limited phonon transport model, we may assume a beam width independent heat capacity. The  $\text{Si}_3\text{N}_4$  volume heat capacity is estimated to be  $0.082T+0.502T^3$  J/ $\text{m}^3\text{-K}$  [13]. The thermal conductivity for wafer B3663 has similar beam width dependence at 21% surface diffusive reflection.

In our detector fabrication for deployment on SPTpol, we have been using  $\text{Si}_3\text{N}_4$  with thermal conductivity similar to that of wafer B1562. Fig. 2 (b) shows the TES Joule heating power as a function of bath temperature of one polarimeter using equation (6). The TES has a  $R - T$  relation in Fig. 3 (b). At  $T=0.450$  K, the 10  $\mu\text{m}$  beam thermal conductivity is 12.87  $\mu\text{W/Kcm}$  using the fit at  $R=0.6$   $\Omega$ .

## 2. Detector Performance

One focus of the polarimeter development has been on controlling the TES transition width. For stable operation the width must be broader than that provided by the Mo/Au TES alone. Fig. 3 (a) shows TES transition width dependence on modification structures. All TESs have two-side PdAu bling. The blue circles are measured using 4-wire method, the others using SQUIDs. The blue circles are for a TES without surface modification. The green squares are for a TES with a 3  $\mu\text{m}$  wide Nb bar in the middle. The magenta diamonds are for a TES with three 3  $\mu\text{m}$  wide Nb bars and 18  $\mu\text{m}$  spacing. The red triangles are for a TES with 3  $\mu\text{m}$  diameter Nb dots and 11  $\mu\text{m}$  row spacing. We find that the three Nb bars with 18  $\mu\text{m}$  spacing slightly increases TES transition width and the 3  $\mu\text{m}$  diameter Nb dots with 11  $\mu\text{m}$  row spacing significantly increases TES transition width. The lateral proximity effect [15] and the tunneling superconducting current between Nb structures [16] may have roles in the TES transition width.

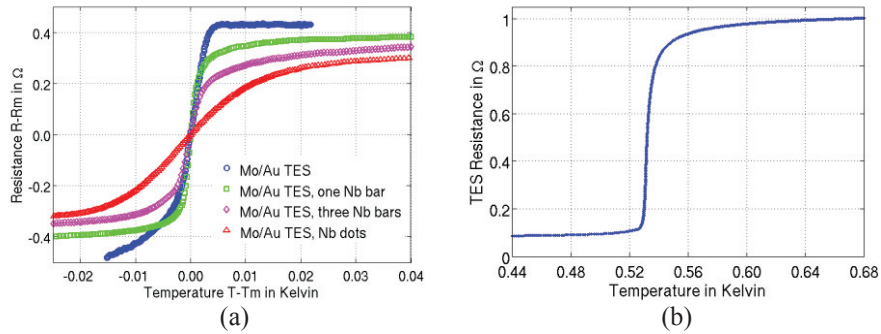


Fig. 3. (a) 23nm Mo and 30nm Au bi-layer TES transition width dependence on surface modification structures.  $R_m=0.645 \Omega$  and  $T_m=0.541 \text{ K}$  for blue circles,  $R_m=0.552 \Omega$  and  $T_m=0.554 \text{ K}$  for green squares,  $R_m=0.495 \Omega$  and  $T_m=0.556 \text{ K}$  for magenta diamonds,  $R_m=0.450 \Omega$  and  $T_m=0.565 \text{ K}$  for red triangles; (b) 22nm Mo and 30nm Au bi-layer TES resistance – temperature relation, the TES has one side PdAu bling and Nb dots with  $18 \mu\text{m}$  row spacing as shown in Fig. 1 (b).

Based on these results, we successfully use  $3 \mu\text{m}$  diameter Nb dots with  $18 \mu\text{m}$  row spacing on top of the TES to define the transition width. Fig. 3 (b) shows the R-T relation of a TES. The  $90 \text{ m}\Omega$  residual resistance is due to PdAu bling. The transition is gradual above  $0.8 \Omega$ , which is useful for polarization angle calibration with high power loading. The temperature change from  $0.8 \Omega$  to  $0.5 \Omega$  is about  $5.1 \text{ mK}$ , which is desirable for a CMB observation with SPT. Fig. 4 (a) shows the Noise Equivalent Power (NEP) spectrum of the TES in dark test. It approximately equals the phonon noise and a  $1/f$  noise.

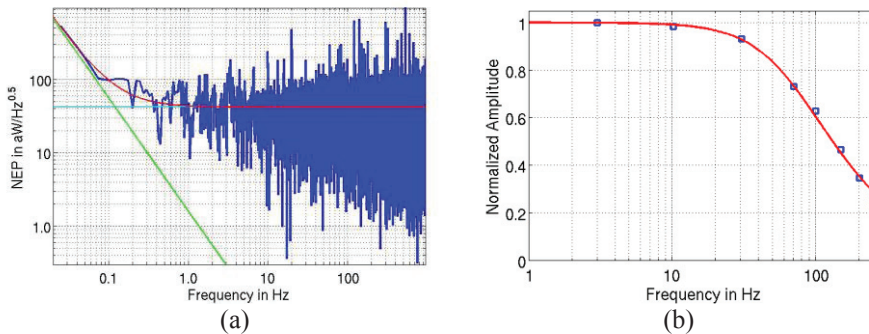


Fig. 4. (a) NEP of a TES at  $R=0.485 \Omega$ . The cyan is the thermodynamic phonon noise floor. The green is a  $1/f$  noise. The red, which is the phonon noise and the  $1/f$  noise, matches the TES noise data in blue; (b) The optical power readout efficiency with TES as a function optical power modulation frequency. The Lorentzian fit line has a time constant of  $2.1 \text{ ms}$ .

The PdAu absorber in the polarimeter dissipates electromagnetic waves polarized along it. The collected optical power and TES Joule heating power heat up the entire  $\text{Si}_3\text{N}_4$  membrane rectangle. The temperature change caused by optical power variation is read out with the TES. The optical power readout efficiency as a function of modulated optical power frequency is measured using a chopped external thermal source for a prototype polarimeter. The normalized modulated optical power readout efficiency as a function of modulation frequency is shown in Fig. 4 (b). The TES is voltage biased at a resistance of  $60\% R_n$ . The measured  $2.1 \text{ ms}$  time constant includes thermal diffusion time from the absorber to the TES and the TES effective time constant.

The optical performance of prototype polarimeters has been tested. The polarimeters have an optical band-pass of 78–110 GHz, an optical power readout efficiency of 80%, and a cross-polarization upper limit of 1% [17].

### 3. Conclusion

We have designed, fabricated, and tested an absorber coupled bolometric polarimeter. The thermal conductance of the detector is understood with a boundary limited phonon transport model, its value is determined by  $\text{Si}_3\text{N}_4$  legs dimensions, and by fraction of phonons diffusive surface reflection which is related to surface roughness [8, 14, 18]. TES transition width is tuned with Nb dots on its surface. Test data show that the absorber-coupled polarimeter has the desired performance in terms of noise, time constant, optical power readout efficiency, and cross polarization.

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